

DRAWINGS

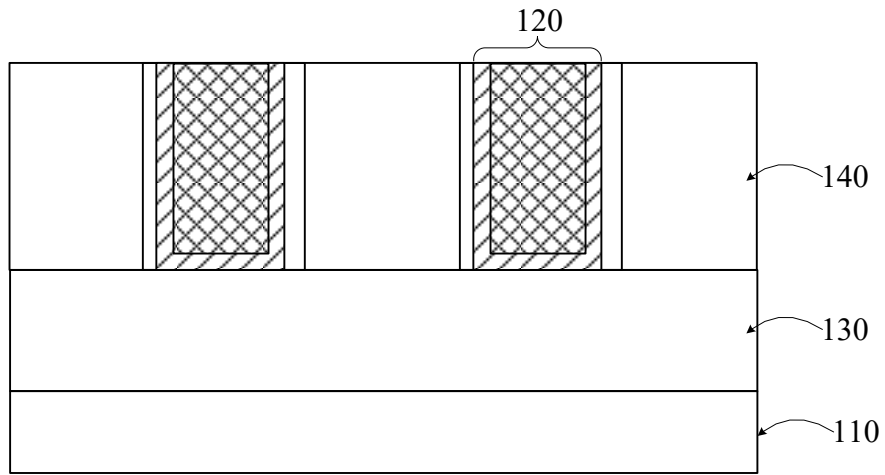


FIG. 1A

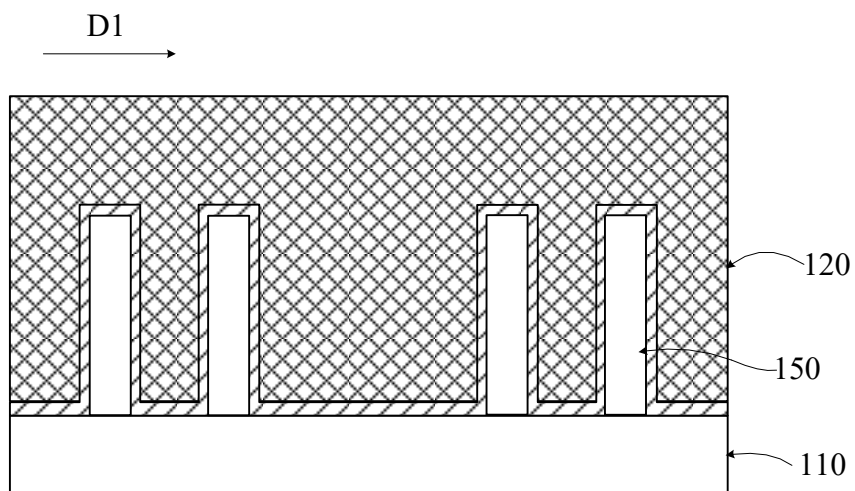


FIG. 1B

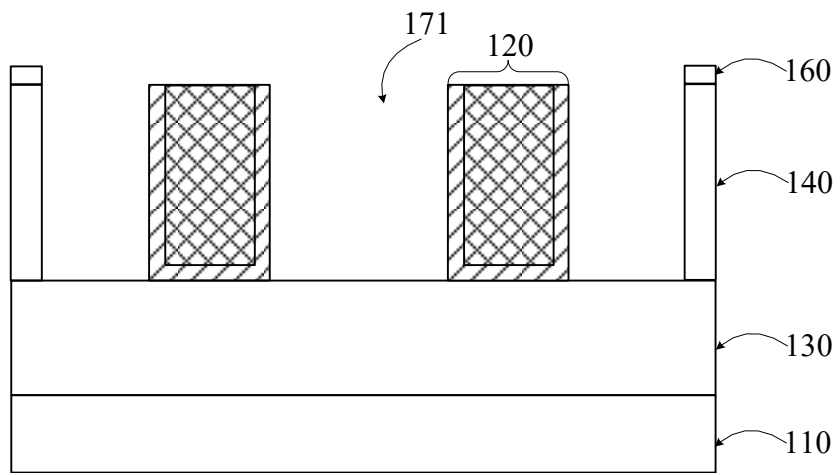


FIG. 1C

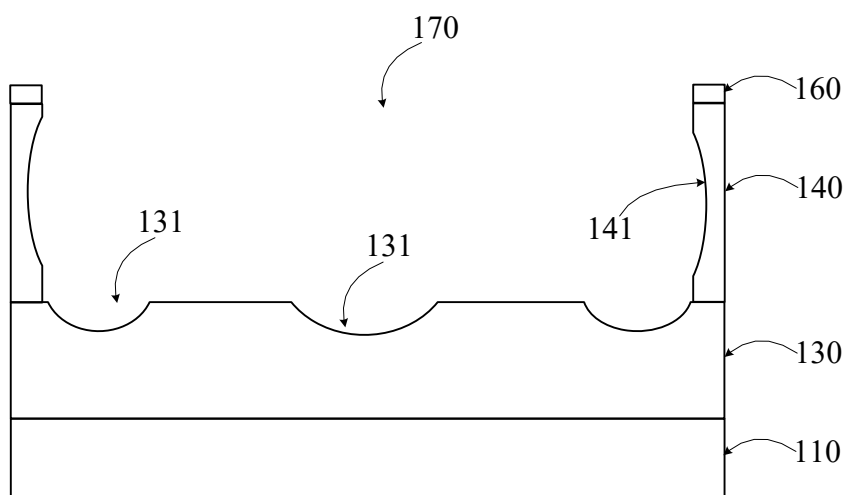


FIG. 1D

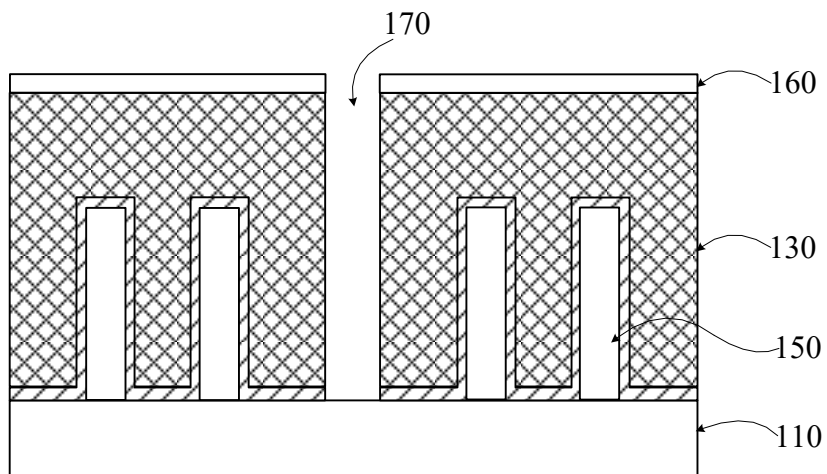


FIG. 1E

provide a to-be-etched object, which includes a substrate, and a gate structure and an isolation dielectric layer which are located on a surface of the substrate, with the gate structure extending along a first direction and being disposed on a same layer as the isolation dielectric layer

S310

alternately and cyclically etch the isolation dielectric layer and the gate structure to form a first isolation trench, which penetrates through the gate structure along a second direction

S320

FIG. 2

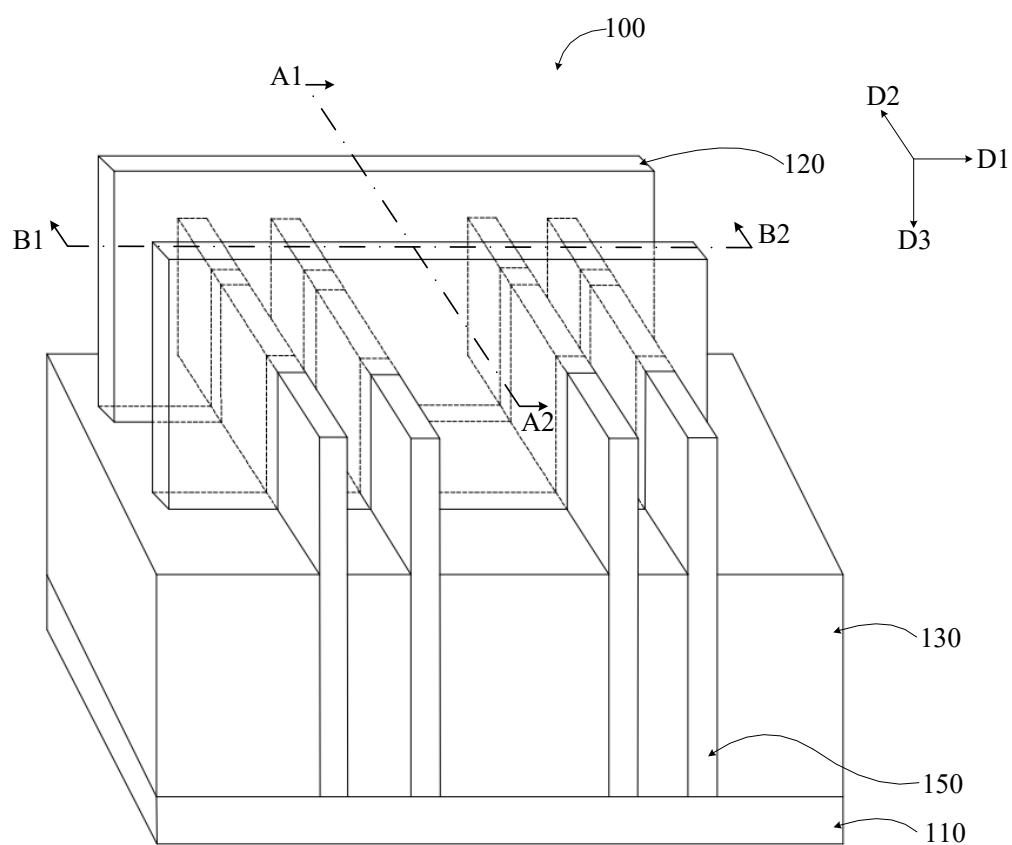


FIG. 3A

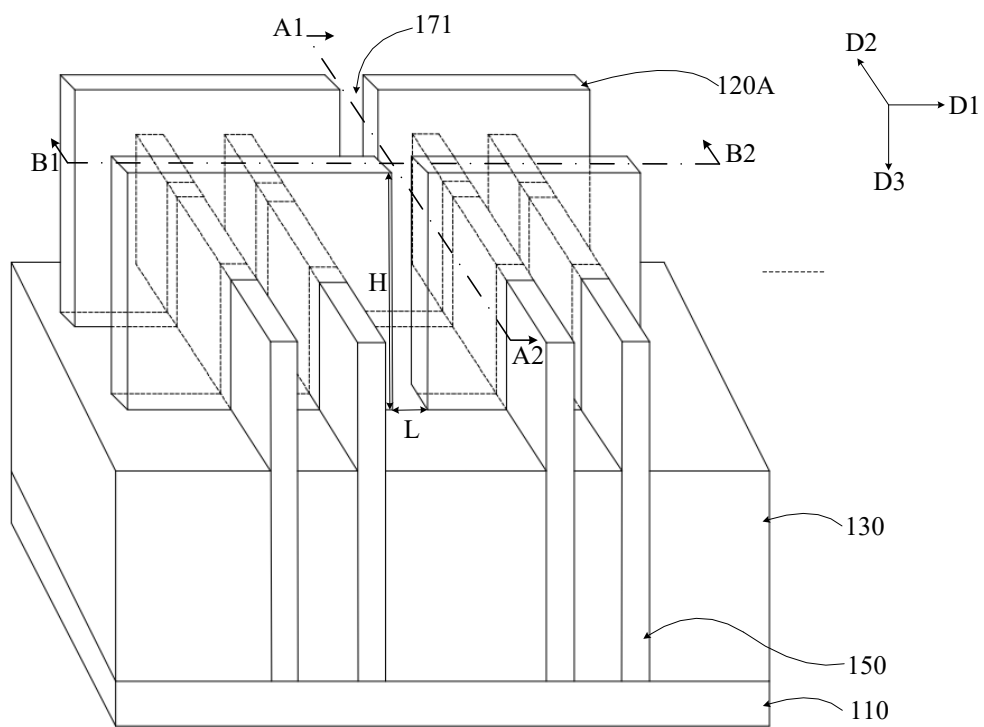


FIG. 3B

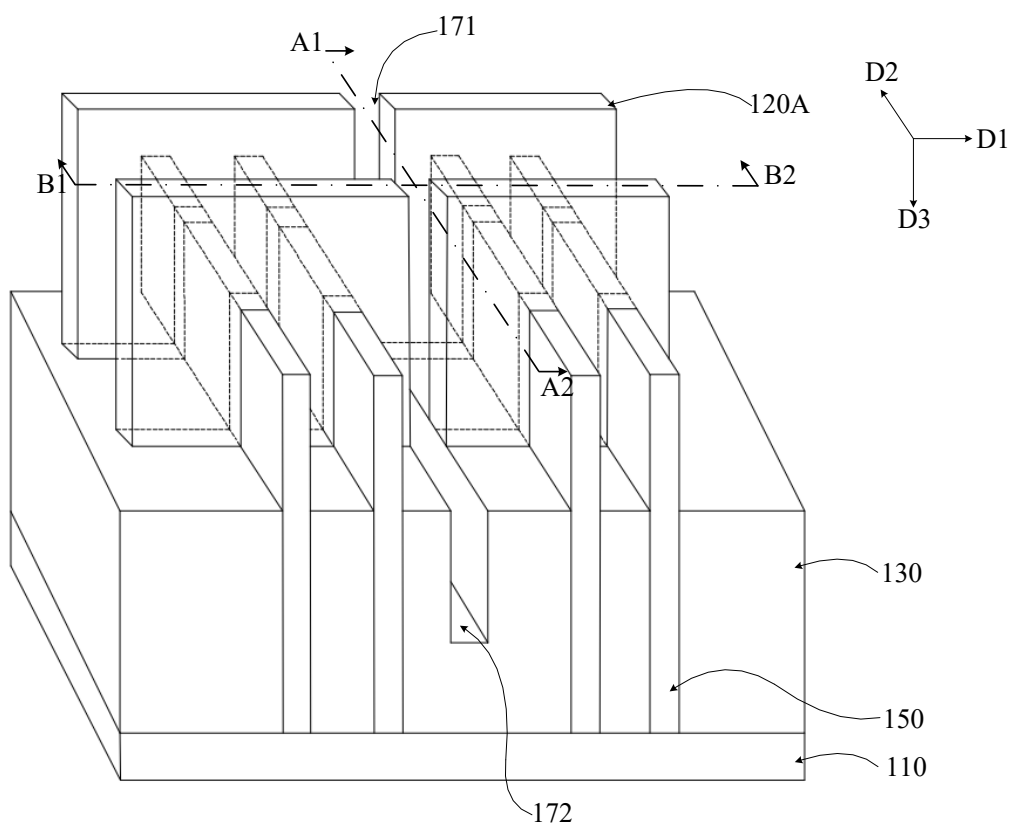


FIG. 3C

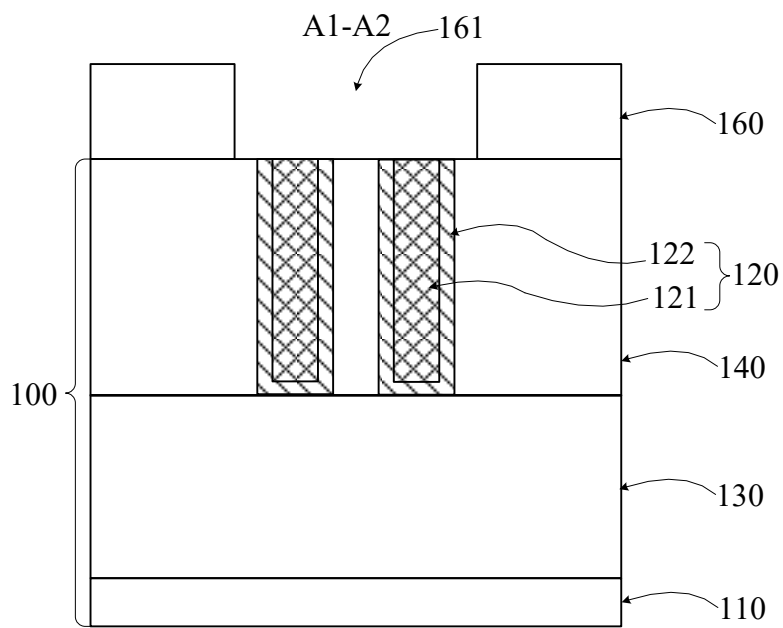


FIG. 4A

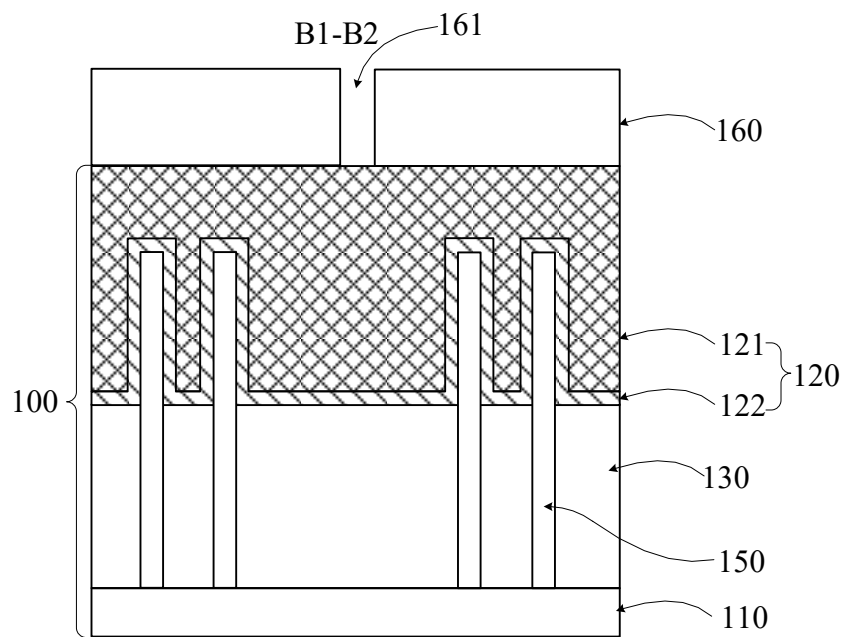


FIG. 4B

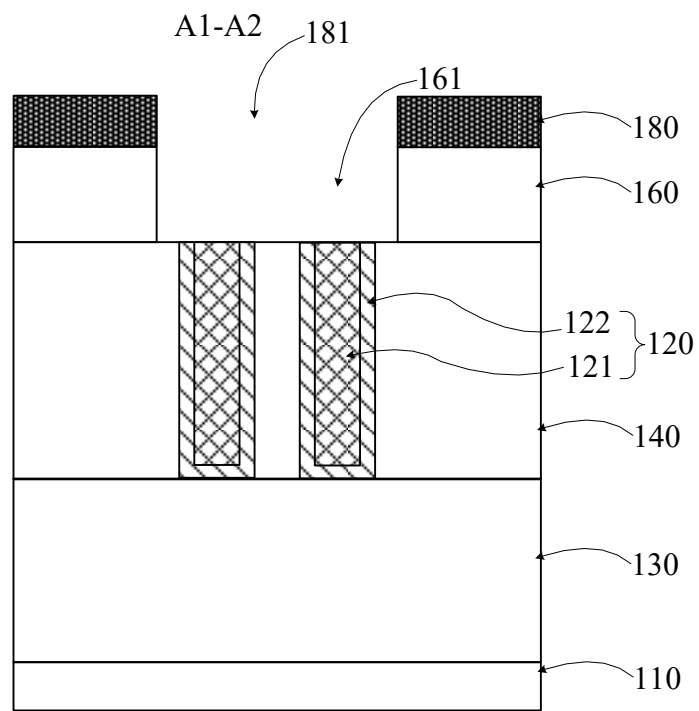


FIG. 5A

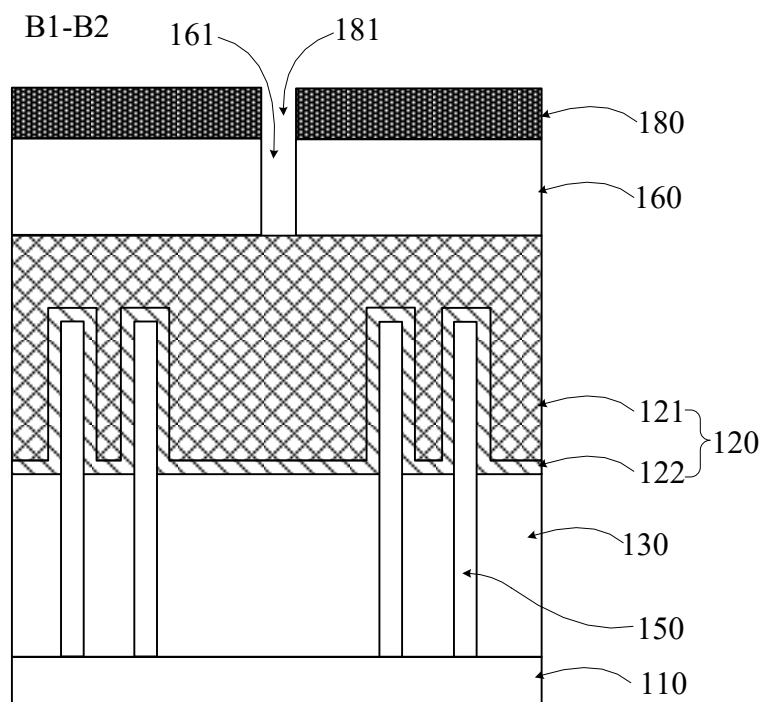


FIG. 5B

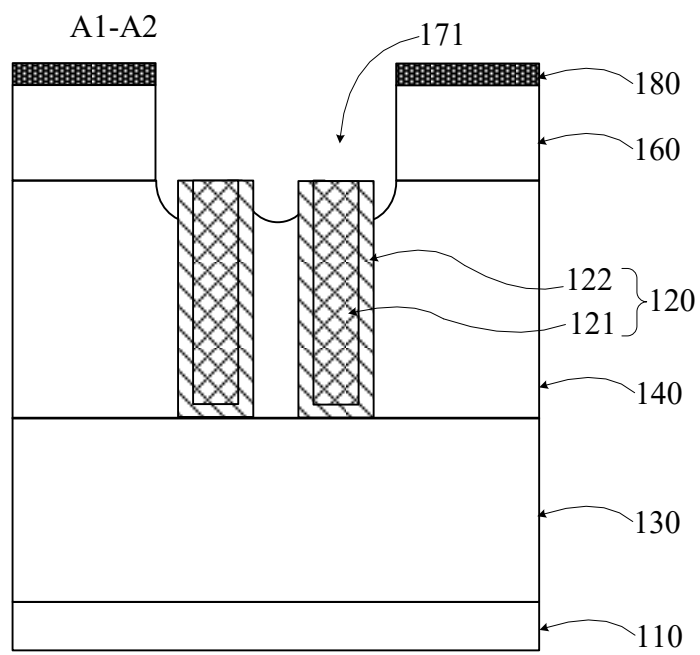


FIG. 6A

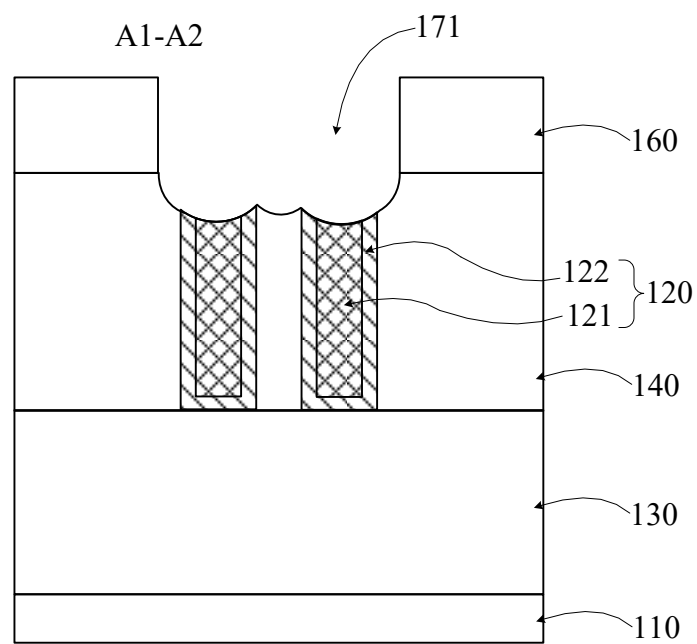


FIG. 6B

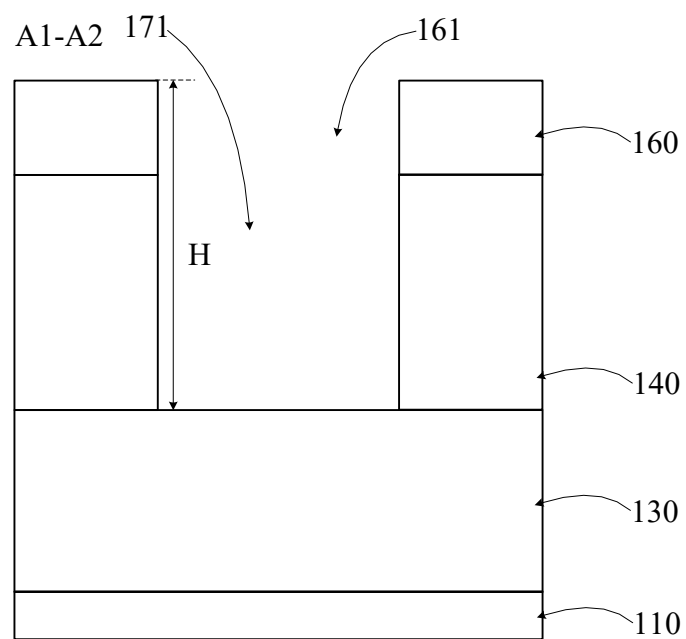


FIG. 7A

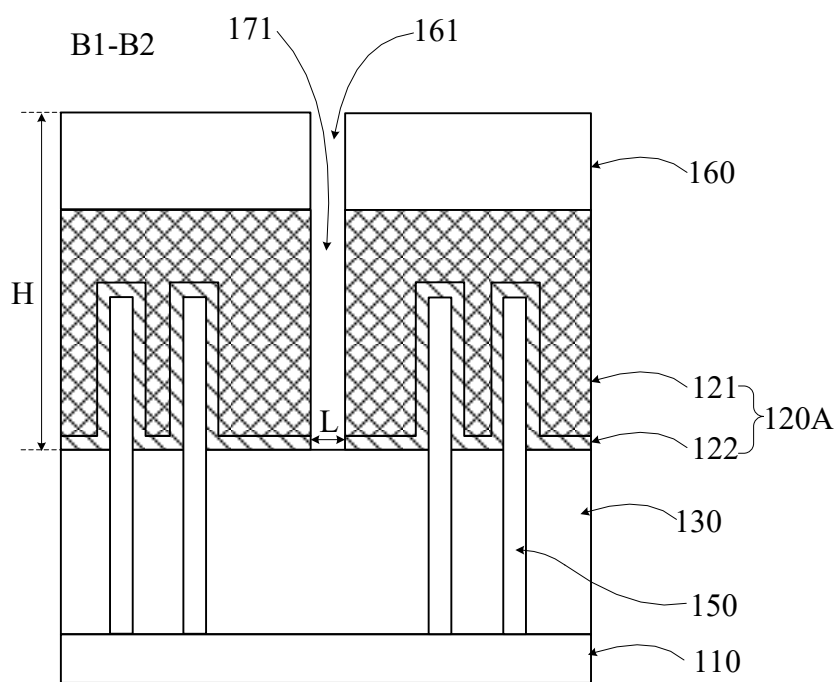


FIG. 7B

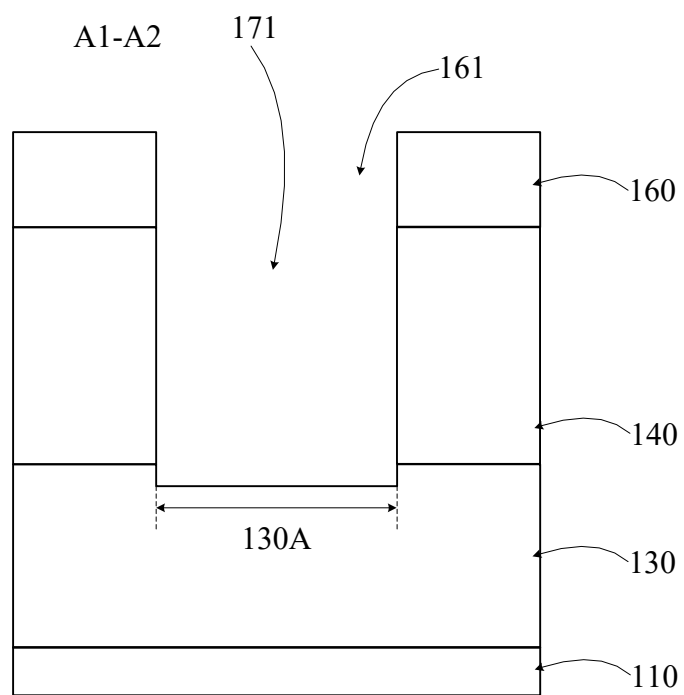


FIG. 8A

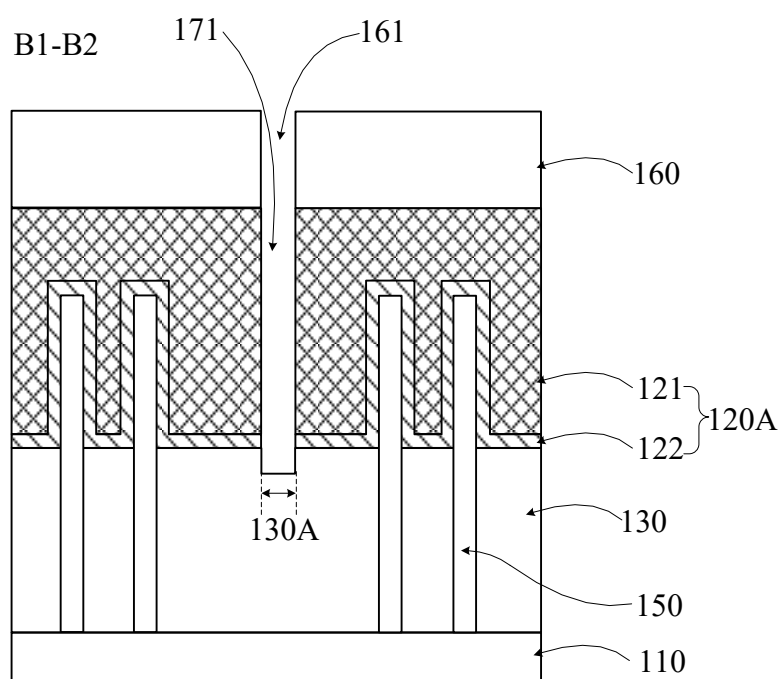


FIG. 8B

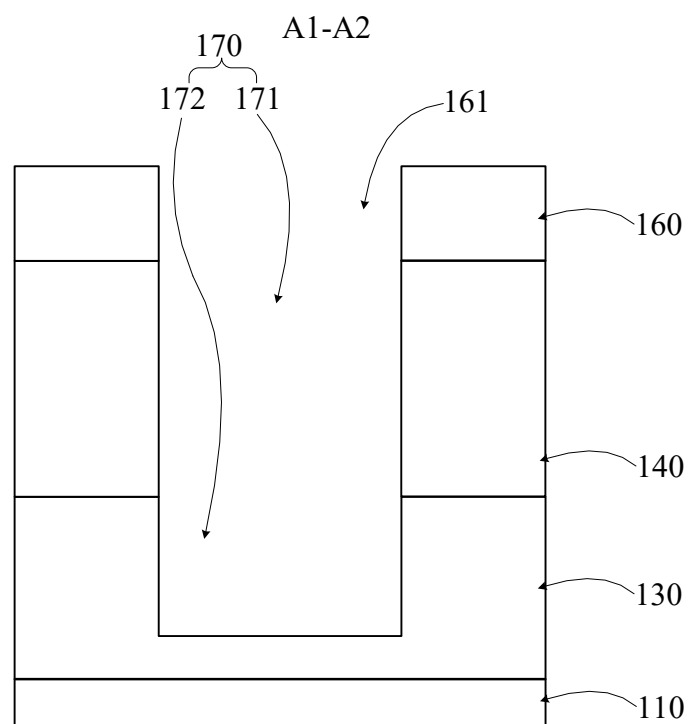


FIG. 9A

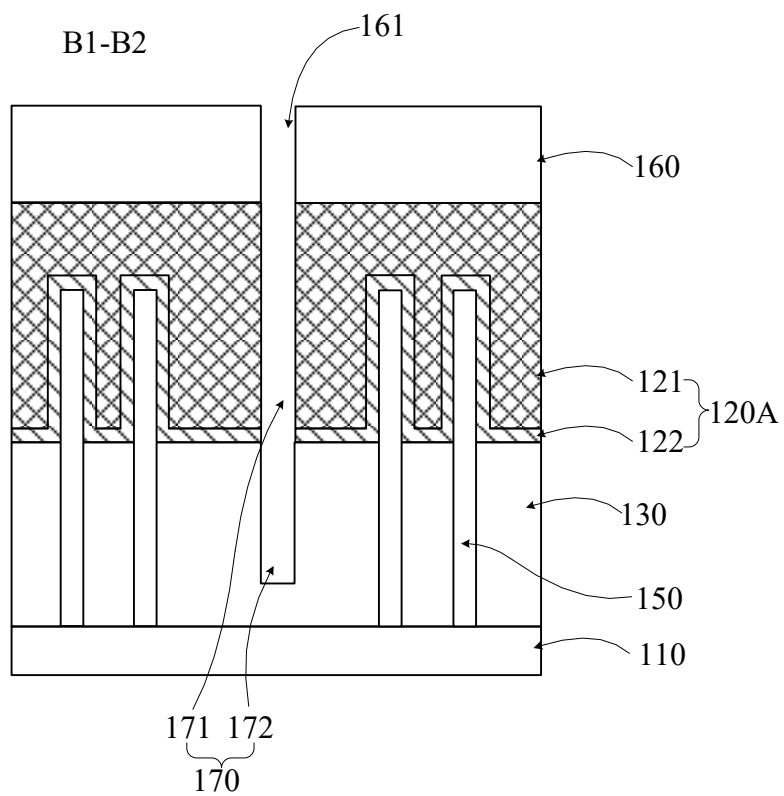


FIG. 9B

200

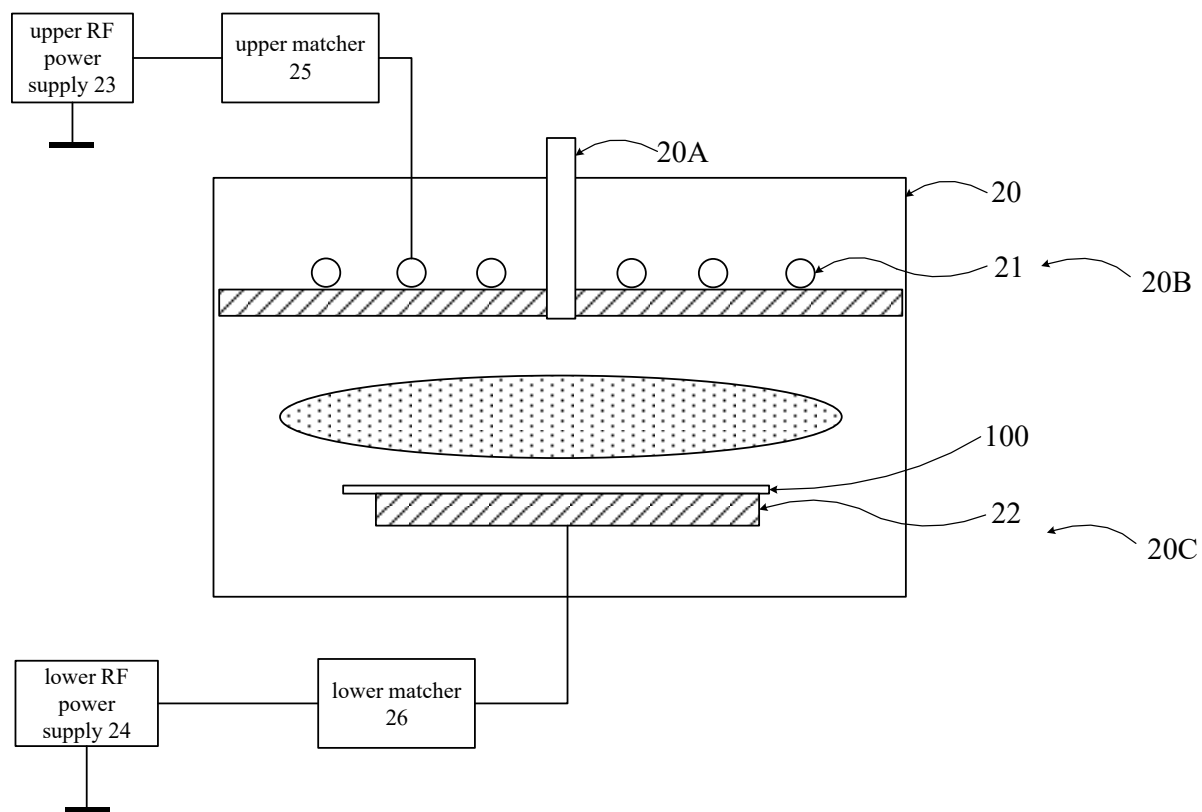


FIG. 10